



FTD2017A

 — N-Channel Silicon MOSFET

Load Switching Applications

Features

- Low ON-resistance.
- 2.5V drive.
- Mounting height 1.1mm
- Composite type, facilitating high-density mounting.
- Drain common specifications.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	I _D		6	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	40	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (1000mm ² ×0.8mm) 1unit	1.3	W
Total Dissipation	P _T	Mounted on a ceramic board (1000mm ² ×0.8mm)	1.4	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0V	20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	0.5		1.3	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =6A	9	13		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =6A, V _{GS} =4.5V		17	23	mΩ
	R _{DS(on)2}	I _D =6A, V _{GS} =4V		18	24	mΩ
	R _{DS(on)3}	I _D =3A, V _{GS} =3.1V		19	30	mΩ
	R _{DS(on)4}	I _D =3A, V _{GS} =2.5V		20	33	mΩ
Input Capacitance	C _{iss}	V _{DS} =10V, f=1MHz		1530		pF
Output Capacitance	C _{oss}	V _{DS} =10V, f=1MHz		230		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =10V, f=1MHz		215		pF

Marking : D2017A

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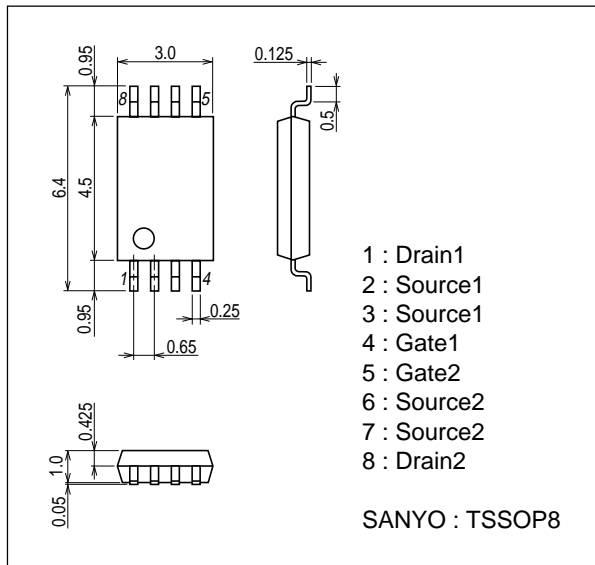
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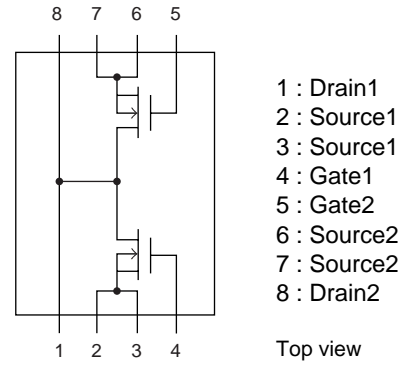
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		19		ns
Rise Time	t_r	See specified Test Circuit.		225		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		125		ns
Fall Time	t_f	See specified Test Circuit.		125		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=4.5V, I_D=6A$		21		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=4.5V, I_D=6A$		3.4		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=4.5V, I_D=6A$		4.8		nC
Diode Forward Voltage	V_{SD}	$I_S=6A, V_{GS}=0V$	0.83	1.2		V

Package Dimensions

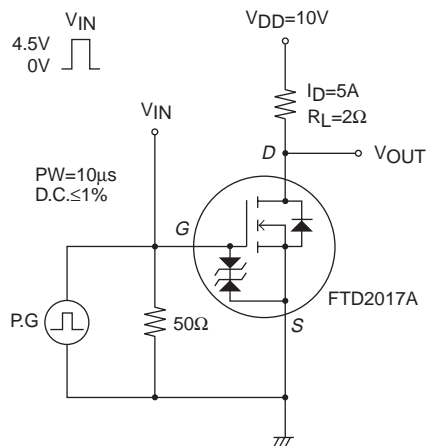
unit : mm (typ)
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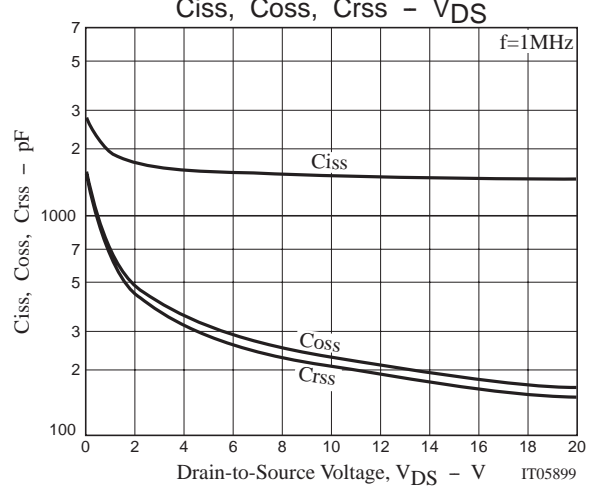
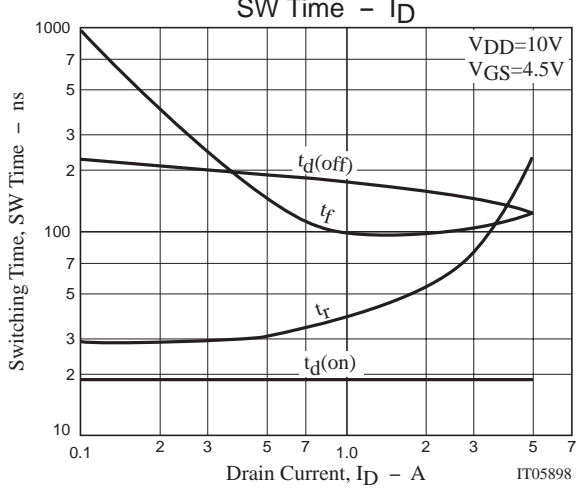
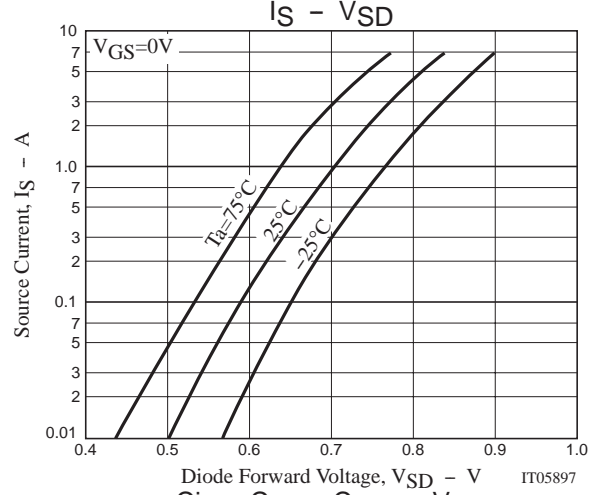
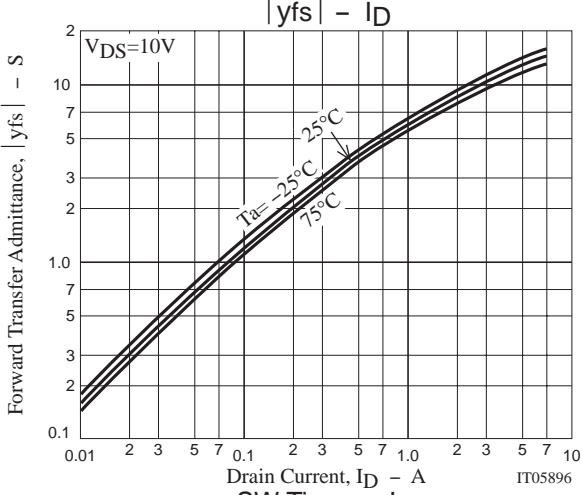
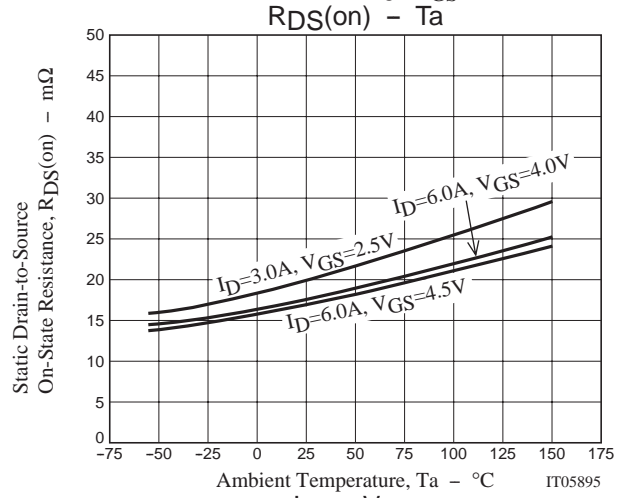
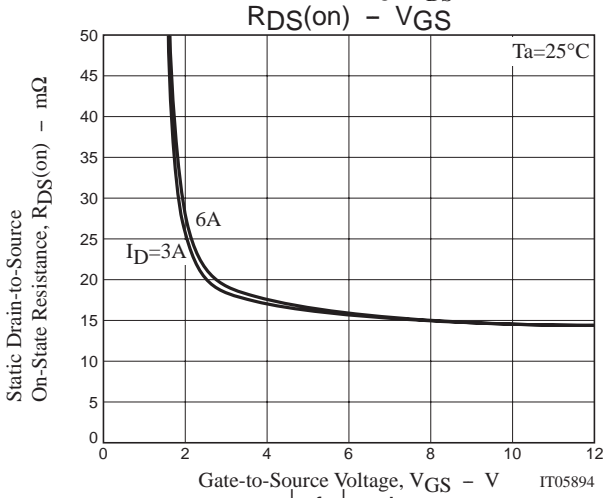
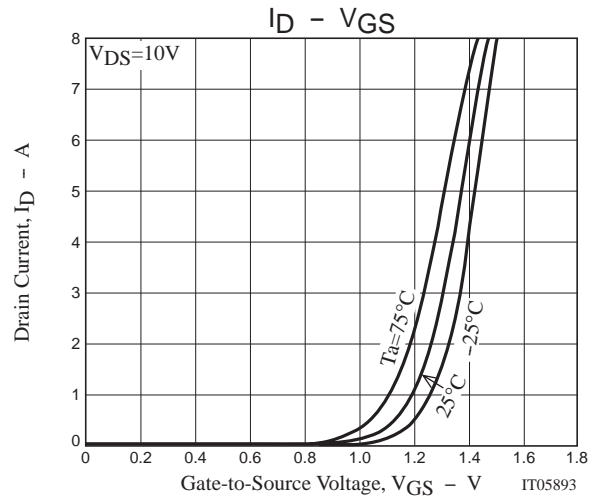
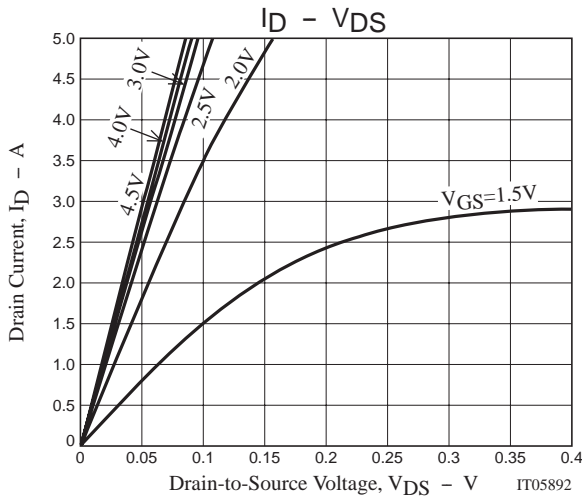
Electrical Connection

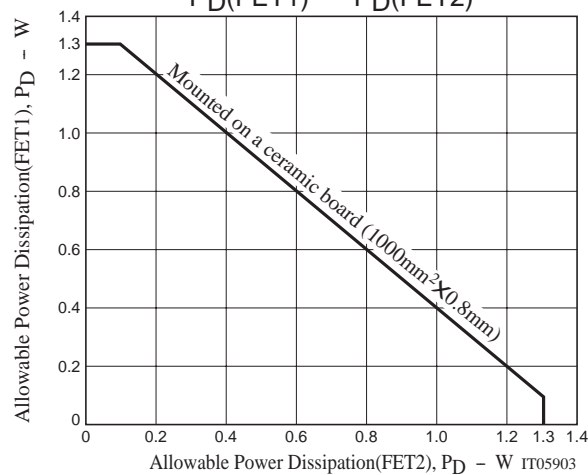
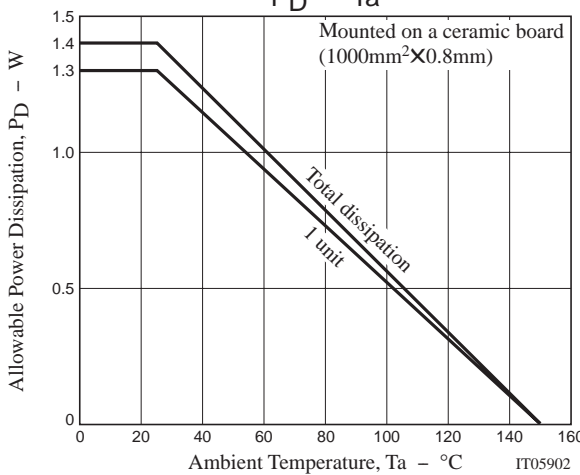
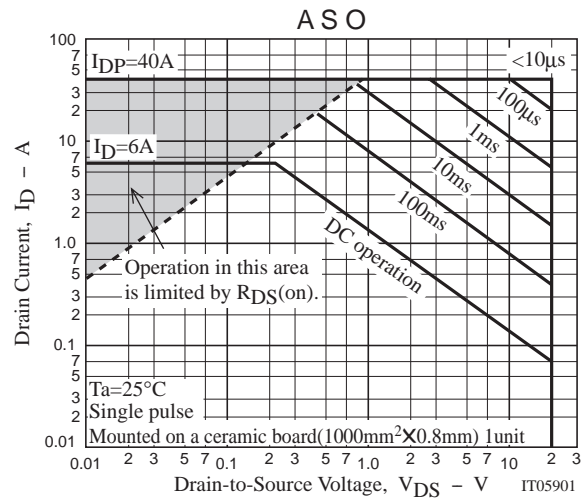
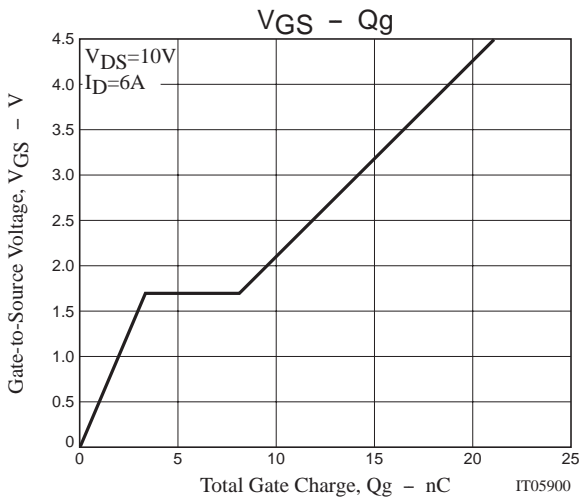


Switching Time Test Circuit



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